

Feature

- High Precision GaAs process
- High performance, shielded
- GaAs substrate, 50Ω CPW output
- Au wire bonding, for MCM applications

Environmental Specifications

Operating Temperature	-55°C~+85°C
Storage Temperature	-65°C~+150°C
Max. Input Power	30dBm

Electrical Specifications(T_A=+25°C)

Parameter	Min.	Typ.	Max.	Unit
Center Freq. (f ₀)	-	14	-	GHz
Pass band	13	-	15	GHz
Insertion Loss	-	-	3.0	dB
VSWR	-	-	1.8	-
Out of band Attenuation	≥30@10~11.5GHz			dBc
	≥30@16.5~26 GHz			dBc
	≥40 @ 0.1~10 GHz			dB

S2P file name: PDBF-13_15-5D3.s2p

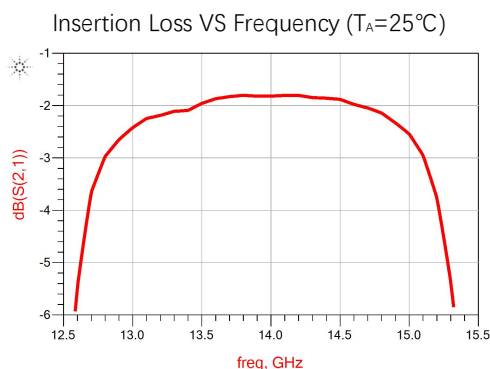
Outline Drawing



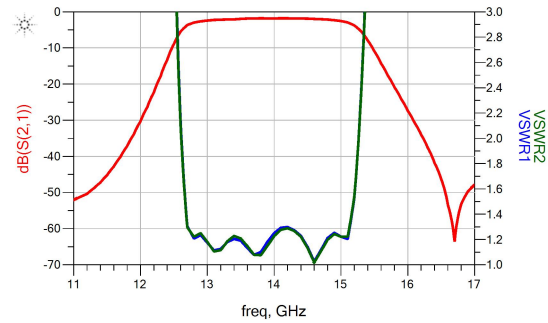
Notes:

1. Dimensions are in millimeters. Tolerance: ±0.05mm
2. Die thickness is 0.15mm
3. Typical bond pad is 0.1x0.1 mm².
4. The bottom of the device is gold plated, should be grounded.

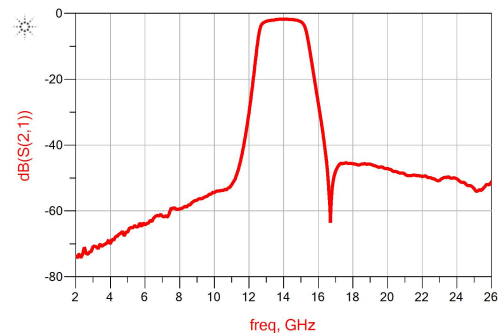
Typical Test Curves



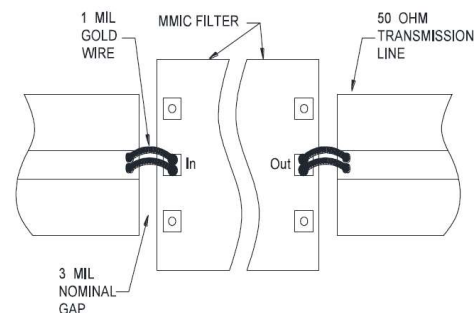
Insertion Loss & Return Loss VS Frequency (T_A=25°C)



Broadband Insertion Loss VS Frequency (T_A=25°C)



Recommended Assembly Diagrams



Application Notes:

1. The chip is back-metallized and can be die-mounted with AuSn eutectic preforms or with electrically conductive epoxy.
2. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (5.8×10⁻⁶/°) with GaAs.
3. Recommend using Φ25um Au wire for bonding, whose length is around 400um.
4. Sinter by AuSn (80/20), which doesn't exceed 300°C within 30 seconds max.
4. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
5. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.
6. The device is sensitive to ESD. ESD protection is required during storage and usage.
7. If you have any questions, please contact us.